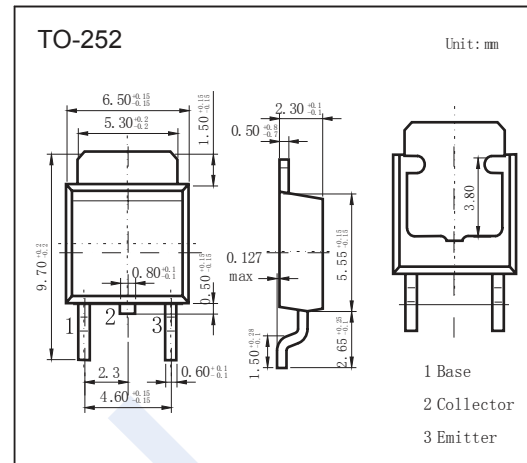


## PNP Transistors

## 2SB1574

## ■ Features

- Collector breakdown voltage:  $V_{CB0}/V_{CE0} = -50V$
- Collector current:  $I_C = -2A$
- For low-frequency output amplification

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-50	V
Collector - Emitter Voltage	$V_{CE0}$	-50	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-2	A
Collector Current - Pulse	$I_{CP}$	-3	
Collector Power Dissipation	$P_C$	10	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu A, I_E = 0$	-50			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1 \text{ mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu A, I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		-0.2	-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$		-0.85	-1.2	
DC current gain	$h_{FE}$	$V_{CE} = -2V, I_C = -200 \text{ mA}$	120		340	
		$V_{CE} = -2V, I_C = -1 \text{ A}$	60			
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1\text{MHz}$		45	60	$\mu F$
Transition frequency	$f_T$	$V_{CE} = -10V, I_E = 50 \text{ mA}, f = 200\text{MHz}$		80		MHz

■ Classification of  $h_{fe}(1)$ 

Type	2SB1574-R	2SB1574-S
Range	120-240	170-340